

## Dimensions

Size: 26 x 13 mils Thickness: 5 mils Bond Pad Size: 5 x 8 mils

# Features

- Capacitance (65 fF Typ.)
- Low Series Resistance (3 Ω Typ.)
- Cut-off Frequency > 500 GHz
- Large Gold Bond Pads

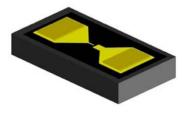
# Specifications @ 25°C (Per Junction)

- V<sub>F</sub> (1 mA): 650–750 mV
- R<sub>S</sub> (10 mA): 7 Ω Max.
- I<sub>R</sub> (3 V): 10 μA Max.
- C<sub>T</sub> (0 V): 80 fF Max.

#### Maximum Ratings

Insertion Temperature	250°C for 10 Seconds		
Incident Power	+20 dBm @ 25°C		
Forward Current	15 mA @ 25°C		
Reverse Voltage	3 V		
Operating Temperature	-55°C to +125°C		
Storage Temperature	-65°C to +150°C		

GaAs Schottky Devices Low R<sub>s</sub> Flip Chip MS8150 - P2613



## Description

The MS8150-P2613 is a GaAs flip chip Schottky diode designed for use as mixer and detector elements at microwave and millimeter wave frequencies. Their high cut-off frequency insures good performance at frequencies to 100 GHz. Applications include: transceivers, digital radios and automotive radar detectors.

These flip chip devices incorporate Microsemi's expertise in GaAs material processing, silicon nitride protective coatings and high temperature metallization. They have large,  $5 \times 8$  mil, bond pads for ease of insertion. The MS8150-P2613 is priced for high volume commercial and industrial applications.

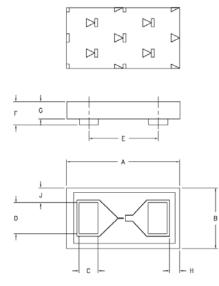
**IMPORTANT:** For the most current data, consult our website: <u>www.MICROSEMI.com</u> Specifications are subject to change. Consult factory for the latest information.

<sup>1</sup> The MS8150 Series of products are supplied with a RoHS complaint Gold finish.

These devices are ESD sensitive and must be handled using ESD precautions



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DIM	INC	HES	MM		
DIM	MIN	MIN MAX		MAX	
А	0.0255	0.0265	0.648	0.673	
В	0.0125	0.0135	0.318	0.343	
С	0.0046	0.0056	0.117	0.142	
D	0.0075	0.0085	0.191	0.216	
E	0.0170	0.0180	0.432	0.457	
F	0.0050	0.0060	0.127	0.152	
G	0.0045	0.0055	0.114	0.140	
Н	0.0016	0.0020	0.041	0.051	
J	0.0023	0.0027	0.058	0.069	

## Spice Model Parameters (Per Junction)

Γ	I <sub>S</sub>	R <sub>S</sub>	Ν	TT	C <sub>J0</sub>	CP	М	EG	VJ	BV	IBV
Γ	А	Ω		Sec	pF	pF		eV	V	V	А
	2 x10 <sup>-13</sup>	3	1.2	0	0.045	0.02	0.50	1.42	0.85	4	1 x 10⁵

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